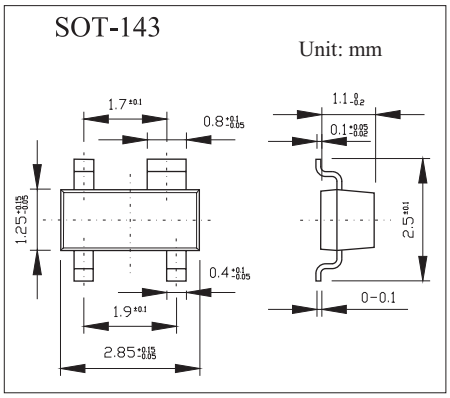
Silicon Switching Diode Array

BAW101



■ Features

● Electrically insulated high-voltage medium-speed diodes

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	300	V
Peak reverse voltage	V_{RM}	300	V
Forward current	I_F	250	mA
Peak forward current	I_{FM}	500	mA
Surge forward current, t = 1 μs	I_{FS}	4.5	A
Total power dissipation, Ts ≤ 35℃	P_{tot}	350	mW
Junction temperature	T_j	150	℃
Storage temperature range	T_{stg}	-65 to +150	℃
Junction - ambient[1)]	$R_{th\ JA}$	≤ 470	K/W
Junction - soldering point	$R_{th\ JS}$	≤ 330	K/W

Note

1.Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm^2 Cu

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V_{BR}	$I_{(BR)}$ = 100 μ A	300			V
Forward voltage	V_F	I_F = 100 mA			1.3	V
Reverse current	I_R	V_R = 250 V			150	nA
		V_R = 250 V, T_A = 150℃			50	μ A
Diode capacitance	C_d	V_R = 0 V, f = 1 MHz		6		pF
Reverse recovery time	t_{rr}	I_F = 10 mA, I_R = 10 mA, R_L = 100 Ω measured at I_R = 1 mA		1		Ω

■ Marking

Marking	JPs